# Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors (ULSIC vs TFT 8)

Sapporo, Hokkaido, Japan 14-18 May 2023

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## Monday, May 15, 2023

06:30 - 08:00	Breakfast (Terrace Brasserie Restaurant)
08:00 – 08:05	<b>Open remark</b> <u>Yue Kuo</u> , Texas A&M University
	Session: General Topics Chair: Yue Kuo, Texas A&M University
08:05 – 08:30	Invited Challenge to next-generation VLSI with VFET using oxide semiconductor and 3D structure1 Shunpei Yamazaki, Semiconductor Energy Laboratory Co., Ltd
08:30 – 08:55	Invited ULSI and TFT technologies joint forces to meet the future challenges of a pervasive digital society2 Olivier Bonnaud, University of Rennes
	<u>Session: Semiconductor Materials</u> Chairs: Kenji Nomura, University of California San Diego Laurie E. Calvet, LPICM, CNRS-Ecole Polytechnique Shinji Migita, AIST
08:55 – 09:20	Invited Atomic-order surface reaction of reactant gas on group IV semiconductor (100) surface3 Junichi Murota, Tohoku University
09:20 – 09:45	Invited Formation and luminescence studies of Ge/Si core-shell quantum dots4 Seiichi Miyazaki, Katsunori Makihara, Yuki Imai, Nagoya University
09:45 – 10:10	Invited Epitaxy and heterostructure of germanium tin-related group-IV alloy semiconductors for future electronic and optoelectronic applications5 Osamu Nakatsuka, Masashi Kurosawa, Shigehisa Shibayama, Mitsuo Sakashita Nagoya University
10:10 – 10:40	Coffee Break
10:40 – 11:00	<b>Crystallinity of In-Ga-Zn-oxide (IGZO) in CAAC-IGZO vertical FET6</b> <u>Tomonori Nakayama</u> , Yukinori Shima, Toshikazu Ono, Nao Sorida, Naoki Okuno, Hitoshi Kunitake, Shunpei Yamazaki, Semiconductor Energy Laboratory Co., Ltd.
11:00 – 11:20	<b>Spinel, an overlooked crystalline phase of Igzo7</b> <u>Hendrik F.W. Dekkers</u> , Akhilesh Kumar Mandal, Evangelos Aggiannis, Adrian Vaisman, Chasin Romain Delhougne, Attilio Belmonte, Gouri Sankar Kar, Interuniversity Microelectronics Centre (imec)

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	Session: P-channel Oxide Materials for TFTs Chair: Olivier Bonnaud, University of Rennes
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11:45 – 12:10	Invited P-channel metal oxide thin film transistors for flexible CMOS logic: Challenges and opportunities9 Andrew Flewitt, <u>Kham Niang</u> , Daisy Gomersall, Jake Meeth, Niels van Fraassen, Sanggil Han, University of Cambridge; James Parish, Andrew Johnson, University of Bath
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14:50 – 15:15	Invited Ferroelectric phase transformation accelerated in nanolaminate HfO2-ZrO2 thin films12 Shinji Migita, The National Institute of Advanced Industrial Science and Technology (AIST)
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18:30 – 20:30	Dinner (Ryusei Room)
20:30 – 21:30	Panel Discussion: Challenges in TFT Materials

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06:30 - 08:00	Breakfast (Terrace Brasserie Restaurant)
	<u>Session: Devices and Circuits I</u> Chairs: Hitoshi Kunitake, Semiconductor Energy Laboratory Co., Ltd I-Chun Cheng, National Taiwan University Radu A. Sporea, University of Surrey
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06:30 - 08:00	Breakfast (Terrace Brasserie Restaurant)
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